



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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TG-CJ-43-43-6-PF

Ceramic Heat Spreader



Features

- Large contact area
- Low weight
- High breakdown voltage
- Excellent heat spreader
- Custom shapes possible

Applications

LED/ NotebookPC/ M/B/ PowerTransistor/ PowerModule/CPU/ ChipIC

Main Component			Al ₂ O ₃
Physical Property	Density	g/cm ³	3.66
	Water Absorption	%	0.002
	Sinter Temperature	°C	1700
	Acid resistance	mg/cm ³	≤ 0.2
	Alkali	mg/cm ³	≤ 0.2
Mechanical Property	Mohs Hardness	HV	9
	Bend Strength	Mpa	≥ 610
	Compression Intensity	Mpa	≥ 620
Thermal Property	Maximum working temperature	°C	1400
	Refractoriness	°C	≥ 1500
	thermal expansion coefficient	(1 x 10 ⁻⁶)mm/°C	7.8 ~ 8.3
	Thermal Shock resistance	T(°C)	200
	Thermal Conductivity	W/m.k	40 ~ 51
Electrical Property	Resisting rate of Volume	Ω. °C	1016
	DC breakdown strength	KV/mm	15.2 ~ 16.7
	Insulation Breakdown Intensity	KV/mm	18
	Dielectric Constant (1MHz)	(E)	10
	Dielectric Dissipation	(tg o)	0.4*10 ⁻³